

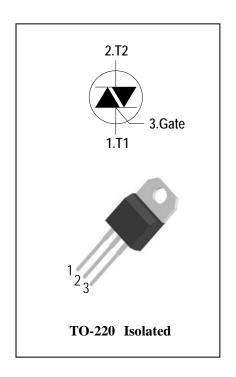
## 4 Quadrants Triacs

#### **General Description**

High current density due to mesa technology . the AIS8D triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, High power motor controls e.g. washing machines and vacuum cleaners,Rectifier-fed DC inductive loads e.g.DC motors and solenoids , motor speed controllers.

#### **Features**

- ◆ Repetitive Peak Off-State Voltage: 600Vand800V
- ◆ R.M.S On-State Current ( I<sub>T(RMS)</sub>= 8A )
- ◆ High Commutation dv/dt
- ◆ These Devices are Pb-Free and are RoHS Compliant
- ◆ Isolated heatsink mounted , Isolation Voltage ( Viso = 2500V AC )



## **Absolute Maximum Ratings**

Symbol	Items	Conditions		Ratings	Unit
V <sub>DRM</sub>	Denetitive Deals Off Chate Valtage	T: - 25°C	AIS8D60	600	V
$V_{RRM}$	Repetitive Peak Off-State Voltage	Tj = 25°C	AIS8D80	800	V
I <sub>T(RMS)</sub>	R.M.S On-State Current	T <sub>C</sub> = 100°C		8	Α
I <sub>TSM</sub>	Surge On-State Current	tp=20ms(50Hz)/tp=16.7ms(60Hz)		80/84	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	tp=10ms		36	A <sup>2</sup> s
-11/-14	Critical rate of rise of on-state	F = 120 Hz Tj = 125°C		50	Δ /
dl/dt	current	rrent $I_G = 2 \times I_{GT}$ , tr $\leq 100 \text{ ns}$		50	A/µs
I <sub>GM</sub>	Peak Gate Current	tp = 20 μs Tj = 125°C		4	Α
$P_{G(AV)}$	Average Gate Power Dissipation(Tj=125°C)			1	W
$P_GM$	Peak Gate Power Dissipation(tp=20us,Tj=125°C)			10	W
Tj	Operating Junction Temperature			- 40 ~ 125	°C
T <sub>STG</sub>	Storage Temperature			- 40 ~ 150	°C





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## **Electrical Characteristics** (Tj = 25°C unless otherwise specified)

Symbol	Items	Conditions		AIS8D60/80				Unit	
					Т	S	Blank	В	
I <sub>DRM</sub>	Peak Forward Reverse Blocking		$V_{DRM} = V_{RRM}, T_{J} = 25^{\circ}C$	Max	5			uA	
I <sub>RRM</sub>	Current		$V_{DRM} = V_{RRM}, T_J = 125^{\circ}C$	Max.	1			mA	
$V_{TM}$	Peak On-Sta	ite Voltage	I <sub>TM</sub> = 11A, t <sub>p</sub> = 380 μs	Max.	1.55			V	
$V_{\sf GD}$	Q1-Q2-Q3-Q4	Non – Trigger Gate Voltage	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 125^{\circ}\text{C}$	Min.	0.2		V		
$V_{GT}$	Q1-Q2-Q3-Q4	GateTrigger Voltage		Max.	1.3		V		
	Q1-Q2-Q3	GateTrigger Current	$V_D = 12V$ , $R_L = 33\Omega$	Max.	5	10	35	50	mA
I <sub>GT</sub>	Q4				10	25	70	100	
lΗ	Q1-Q2-Q3-Q4	Holding Current	I <sub>T</sub> = 0.1A	Max.	10	25	35	60	mA
	Q1-Q3-Q4	1.4.1	1 101		15	30	40	60	
IL	I <sub>H</sub> Q1-Q2-Q3-Q4         Holding Current           I <sub>L</sub> Q1-Q3-Q4         Latching Current	I <sub>G</sub> = 1.2 I <sub>GT</sub>	Max.	20	40	60	90	mA	
dV/dt	Critical Rate of Rise of Off-State Voltage		$V_D = 2/3V_{DRM}$ gate open $Tj = 125^{\circ}C$	Min.	10	20	200	400	V/µs
(dV/dt)c	Rate of Change of Commutating Current,		(dl/dt)c=-3.5A/ms Tj = 125°C	Min.	1	2	5	10	V/µs
R <sub>th(j-c)</sub>	Junction to case (AC)		Max.	2.5			°C/W		
R <sub>th(j-a)</sub>	Junction to ambient		Max.	60			°C/W		

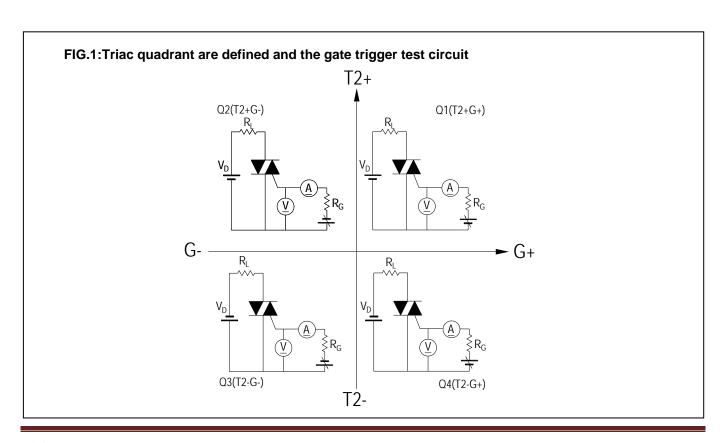




FIG.2: Maximum on-state power dissipation

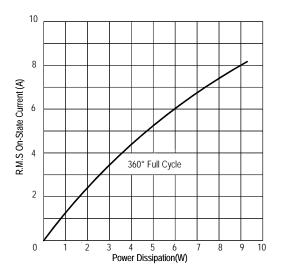


FIG.4: Maximum transient thermal impedance

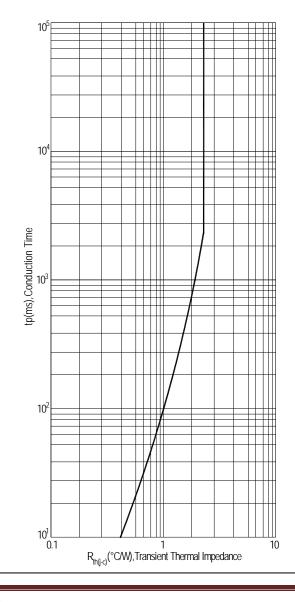


FIG.3: Typical RMS on-state current VS Allowable case Temperature

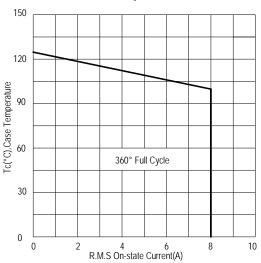


FIG.5: Rated surge on-state current (Non-Repetitive)

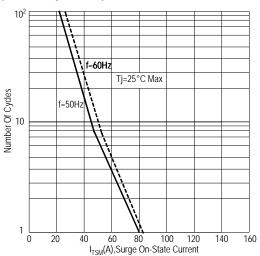


FIG.6: Gate trigger current VS Junction temperature

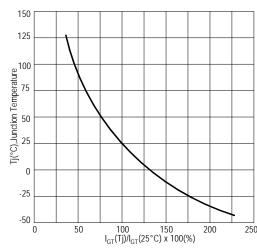




FIG.7:Holding current and Latching current VS Junction temperature

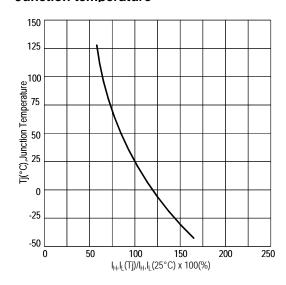


FIG.8: Gate trigger voltage VS Junction temperature

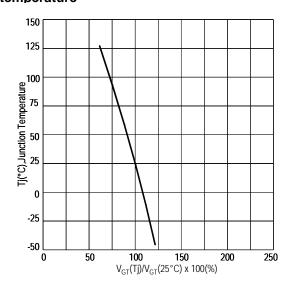
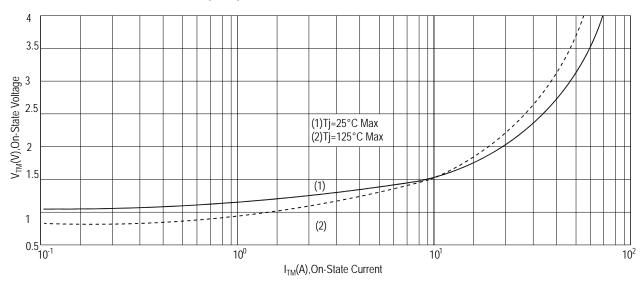


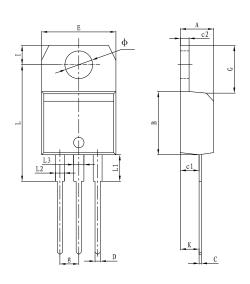
FIG.9: On-state characteristics(Max)



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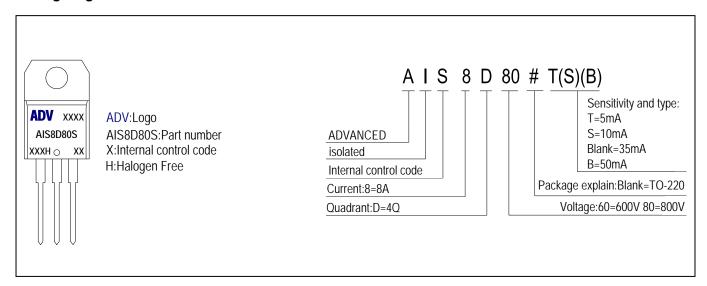


# PACKAGE MECHANICAL DATA TO-220(isolated) Package Dimension



	Dimer	nsions	Dimensions			
Symbol	In Millimeters		In Inches			
	Min	Max	Min	Max		
Α	4.40	4.60	0.173	0.181		
В	9.00	9.30	0.354	0.366		
С	0.40	0.60	0.015	0.023		
c1	2.00	2.60	0.078	0.102		
c2	1.23	1.32	0.048	0.051		
D	0.70	1.00	0.027	0.039		
Е	10.00	10.40	0.393	0.409		
g	2.40	2.70	0.094	0.106		
G	6.20	6.80	0.244	0.267		
ı	2.65	2.95	0.104	0.116		
L	15.80	16.80	0.622	0.661		
L1	3.75		0.147			
L2	1.14	1.70	0.044	0.066		
L3	1.14	1.70	0.044	0.066		
Ф	3.60	3.90	0.141	0.153		
К	2.60TYP		0.102TYP			

### **Making Diagram**



## **Ordering information**

Part number	Part number Package		Packing	Quantity			
AIS8D60#	TO-220 isolated	AIS8D60#	Tube	50pcs			
AIS8D80#	TO-220 isolated	AIS8D80#	Tube	50pcs			
Note:# = Gate Trigger Current Sensitivity and type							



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